

Metal-Dimer Atomic Reconstruction Leading to Deep Donor States of the Anion Vacancy in II-VI and Chalcopyrite Semiconductors

Se a La a d A e Z, e

National Renewable Energy Laboratory, Golden, Colorado 80401, USA

(Received 13 August 2004; published 5 October 2004)

First-principles calculations reveal that the reconstruction of the anion vacancy in II-VI and chalcopyrite semiconductors leads to the formation of deep donor states. The energy levels of these states are shown to be sensitive to the reconstruction geometry. The results are compared with experimental data and previous theoretical work.

DOI: 10.1103/PhysRevLett.93.156404

PACS numbers: 71.15.Mb, 71.20.Nr, 71.55.Gg

Vacancies in II-VI and chalcopyrite semiconductors are known to be deep donors. The reconstruction of the anion vacancy leads to the formation of deep donor states. The energy levels of these states are shown to be sensitive to the reconstruction geometry. The results are compared with experimental data and previous theoretical work.

The energy levels of the deep donor states are shown to be sensitive to the reconstruction geometry. The results are compared with experimental data and previous theoretical work.

and chalcopyrite semiconductors are known to be deep donors. The reconstruction of the anion vacancy leads to the formation of deep donor states. The energy levels of these states are shown to be sensitive to the reconstruction geometry. The results are compared with experimental data and previous theoretical work.

Z Se a d CuGaSe₂ [20]. T e LDA ba d a e
c ec ed b ac ed a e ca d a e

$a_1(a)$ b a
 Z Se ($CuGaSe_2$) $E_v + 1.1$ eV ($E_v + 0.2$ eV), b e
 $E_v + 0.2$ eV ($E_v - 2.5$ eV), a e e a a .
 T , a , a e d , b c c e d a_1^2 e e c a e d
 Z Se , a b e e VBM , e e a $CuGaSe_2$
 dee *inside* e a e c e b a d . W e V_{Se}^0 e d c e ,
 e e a_1^0 c , a V_{Se}^{2+} (F . 1), a
 b e a , e e a - e a d e (Table I), a d a e ,
 e a T_d a c e e (F . 1, b). T e
 e - a c e e e e e a_1 a e Z Se e
up $E_v + 0.2$ eV (V_{Se}^0) $E_v + 2.5$ eV (V_{Se}^{2+}), e e a
 $CuGaSe_2$ e *up* $E_v - 2.5$ eV (V_{Se}^0) $E_v +$
 1.5 eV (V_{Se}^{2+}) [20]. T a a c e a a e d
 c e e c a b e , d e d e a c a
 e e c a c e e c , .e., e e e e e e c c
 C , b e , d e e a_1^2 (V_{Se}^0) \rightarrow a_1^0 (V_{Se}^{2+}) a -
, , d a e d a c e a_1 e e a d *lower*
 e e e . B e c a e e c a e a e d e d e
 e d e c e e *below* VBM *above* VBM , e
 Se a c c a c e c a a , e a e a a b e
 c , a , c e e c a e a e d
 e VBM e d e c e e , e e a e e e .
 T , e Se a c c a e a e e e e -

